

RELIABILITY REPORT  
FOR  
MAX2688EWS+T  
WAFER LEVEL PRODUCTS

June 4, 2013

**MAXIM INTEGRATED**

160 RIO ROBLES  
SAN JOSE, CA 95134

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**Conclusion**

The MAX2688EWS+T successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

**Table of Contents**

<b>I. ....Device Description</b>	<b>IV. ....Die Information</b>
<b>II. ....Manufacturing Information</b>	<b>V. ....Quality Assurance Information</b>
<b>III. ....Packaging Information</b>	<b>VI. ....Reliability Evaluation</b>
<b>.....Attachments</b>	

**I. Device Description**

## A. General

The MAX2686/MAX2688 low-noise amplifiers (LNAs) are designed for GPS L1, Galileo, and GLONASS applications. Designed in Maxim's advanced SiGe process, the devices achieve high gain and ultra-low-noise figure while maximizing the input-referred 1dB compression point and the 3rd-order intercept point. The MAX2686 provides a high gain of 19dB. The MAX2688 supplies 15dB of gain while attaining higher linearity. The devices operate from a +1.6V to +3.3V single supply. The optional shutdown feature in the devices reduces the supply current to less than 10 $\mu$ A. The devices are available in a very small, lead-free, RoHS-compliant, 0.86mm x 0.86mm x 0.65mm wafer-level package (WLP).

## II. Manufacturing Information

A. Description/Function:	GPS/GNSS Low-Noise Amplifiers
B. Process:	MB3
C. Number of Device Transistors:	1057
D. Fabrication Location:	USA
E. Assembly Location:	Japan
F. Date of Initial Production:	July 30, 2010

## III. Packaging Information

A. Package Type:	4-bump WLP 2x2 array
B. Lead Frame:	N/A
C. Lead Finish:	N/A
D. Die Attach:	None
E. Bondwire:	N/A (N/A mil dia.)
F. Mold Material:	None
G. Assembly Diagram:	#05-9000-4074
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	°C/W
K. Single Layer Theta Jc:	°C/W
L. Multi Layer Theta Ja:	103°C/W
M. Multi Layer Theta Jc:	°C/W

## IV. Die Information

A. Dimensions:	33.86 X 33.86 mils
B. Passivation:	BCB
C. Interconnect:	Al with top layer 100% Cu
D. Backside Metallization:	None
E. Minimum Metal Width:	0.23 microns (as drawn)
F. Minimum Metal Spacing:	0.23 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO <sub>2</sub>
I. Die Separation Method:	Wafer Saw

## V. Quality Assurance Information

- A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)  
Don Lipps (Manager, Reliability Engineering)  
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.  
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

## VI. Reliability Evaluation

### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 48 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 22.9 \times 10^{-9}$$

$$\lambda = 22.9 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maximintegrated.com/qa/reliability/monitor>. Cumulative monitor data for the MB3 Process results in a FIT Rate of 0.05 @ 25C and 0.89 @ 55C (0.8 eV, 60% UCL)

### B. E.S.D. and Latch-Up Testing (lot SI3YCQ001E, D/C 1017)

The WV21-5 die type has been found to have all pins able to withstand a HBM transient pulse of +/- 2500V per JEDEC JESD22-A114. Latch-Up testing has shown that this device withstands a current of +/- 250mA and overvoltage per JEDEC JESD78.

**Table 1**  
Reliability Evaluation Test Results

**MAX2688EWS+T**

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
<b>Static Life Test</b> (Note 1)	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	48	0	SI3YCQ001E, D/C 1017

Note 1: Life Test Data may represent plastic DIP qualification lots.